

	Type	Hits	Search Text
1	BRS	17644	(insulated adj gate adj bipolar adj transistor) or IGBT or (MOS adj controlled adj thyristor) or MCT or (gate adj turn-off adj thyristor) or GTO or (insulat\$3 adj gate adj bi-polar adj transistor) or (metal adj oxide adj semiconductor adj controll\$4 adj thyristor) or (gate adj turnoff adj thyristor)
2	BRS	0	((insulated adj gate adj bipolar adj transistor) or IGBT or (MOS adj controlled adj thyristor) or MCT or (gate adj turn-off adj thyristor) or GTO or (insulat\$3 adj gate adj bi-polar adj transistor) or (metal adj oxide adj semiconductor adj controll\$4 adj thyristor) or (gate adj turnoff adj thyristor)) and (diffu\$4 near8 n near8 uniform\$4 near8 (wafer\$3 or substrate\$3))
3	BRS	49	diffu\$4 near8 n near8 uniform\$4 near8 (wafer\$3 or substrate\$3)
4	BRS	74350	(diffus\$4) near8 (wafer\$3 or substrate\$3)
5	BRS	822	((insulated adj gate adj bipolar adj transistor) or IGBT or (MOS adj controlled adj thyristor) or MCT or (gate adj turn-off adj thyristor) or GTO or (insulat\$3 adj gate adj bi-polar adj transistor) or (metal adj oxide adj semiconductor adj controll\$4 adj thyristor) or (gate adj turnoff adj thyristor)) and ((diffus\$4) near8 (wafer\$3 or substrate\$3))
6	BRS	1322766	thin or thinning or thinned or CMP or planariz\$4 or (chemical adj vapor adj deposit\$4)

	DBs	Time Stamp
1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:28
2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:30
3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:43
4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:44
5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:44
6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/20 16:45

	Type	Hits	Search Text
7	BRS	462	((insulated adj gate adj bipolar adj transistor) or IGBT or (MOS adj controlled adj thyristor) or MCT or (gate adj turn-off adj thyristor) or GTO or (insulat\$3 adj gate adj bi-polar adj transistor) or (metal adj oxide adj semiconductor adj controll\$4 adj thyristor) or (gate adj turnoff adj thyristor)) and ((diffus\$4) near8 (wafer\$3 or substrate\$3))) and (thin or thinning or thinned or CMP or planariz\$4 or (chemical adj vapor adj deposit\$4))
8	IS&R	176	(438/138).CCLS.
9	IS&R	337	(438/309).CCLS.
10	IS&R	152	(438/212).CCLS.
11	IS&R	174	(438/311).CCLS.
12	IS&R	40	(438/331).CCLS.
13	IS&R	123	(438/273).CCLS.

	DBs	Time Stamp
7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:17
8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:32
9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:38
10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 13:50
11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 14:07
12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 14:07
13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 14:30